Stri-Il (M) Repeal (16/14/3

SEM 2-5 (RC 07-08)

F.E. (Semester – II) Examination, Nov./Dec. 2013 (Revised in 2007-08)

BASIC ELECTRONIC ENGINEERING

Duration: 3 Hours Total Marks: 100

Instructions: 1) Answer five questions, choosing at least one from each Module.

- 2) Assume any additional data, if required.
- 3) Graph papers will be provided on request.

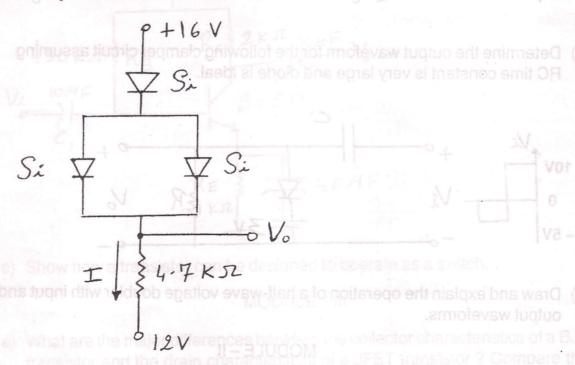
MODULE-I

1. a) Draw a reverse-biased pn junction and explain the following terms:

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- i) Potential barrier
- ii) Reverse saturation current.
- b) Explain the three diode equivalent circuits along with their V-I characteristics. 6
- c) Find V_o and I for the given network.

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d) Derive the ripple factor for a center-tapped full wave rectifier.

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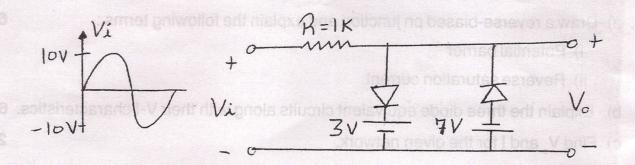
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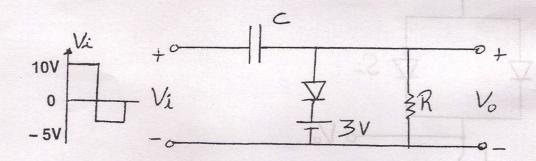
- 2. a) A bridge rectifier uses load resistor $R_L = 2k\Omega$. Each diode has a slope resistance $R_f = 10\Omega$. Input voltage V_i in each half cycle has amplitude of 20 Volts and frequency is 50 Hz. Calculate:
 - i) Peak, dc and rms values of load current.
 - ii) dc output voltage.

Expend (16/14,3

- b) Why is a filter required in a dc power supply? Draw the circuit of a C-filter and the output waveform.
- c) Analyze and draw the output waveform for the following biased parallel clipper. Assume ideal diodes.



 Determine the output waveform for the following clamper circuit assuming RC time constant is very large and diode is ideal.



e) Draw and explain the operation of a half-wave voltage doubler with input and output waveforms.

MODULE-II

3. a) Derive the relationship between the leakage currents in the Common Base (CB) and Common Emitter (CE) transistors.

- b) Draw the circuit setup and explain how the static output characteristics of CB (npn) transistor are plotted.

c) Explain how a CE transistor can be used as an amplifier.

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- 4. a) i) Explain the parameters to which the collector current of a transistor is sensitive to.
 - ii) Derive the stability Factor S(I_{co}) for a fixed bias circuit.

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b) For the given emitter bias network, determine

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a) I

b) 10

c) V_{CE}

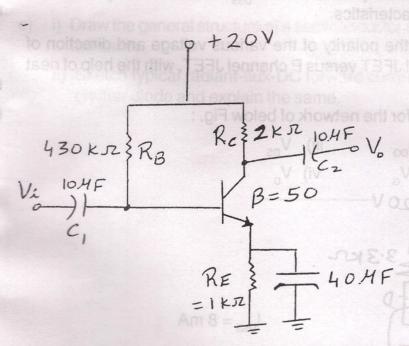
d) V_c

e) V_E

f) V_R

g) V_{BC}

h) I_{Csat}



c) Show how a transistor can be designed to operate as a switch.

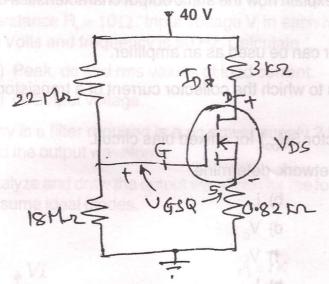
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MODULE-III

5. a) What are the major differences between the collector characteristics of a BJT transistor and the drain characteristics of a JFET transistor? Compare the units of each axis and the controlling variable. How does I_c react to increasing level of I_B versus change in I_D to increasingly negative value of V_{GS}?

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b) Determine I_{DQ} , V_{GSQ} and V_{DS} for the network of Fig. given below :

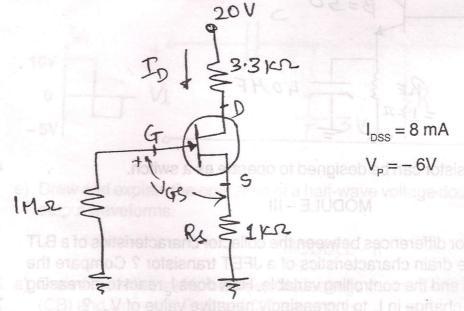


for 2 N4351

$$V_{GS(TH)} = 5V$$

$$I_{D(ON)} = 3 \text{ mA}$$

- c) A p-channel JFET has device parameters of $I_{DSS} = 7.5$ mA and $V_p = 4V$. Sketch the transfer characteristics.
- a) In general comment on the polarity of the various voltage and direction of currents for an n-channel JFET versus P channel JFET, with the help of neat labelled sketches.
 - b) Determine the following for the network of below Fig. :



c) Write short note on CMOS Inverter.

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MODULE-IV

7.	a)	Explain the various steps involved in the fabrication of monolithic ICs.	10
	b)	Draw a Wein bridge oscillator and write the expression for the frequency of oscillation.	3
	c)	Sketch the typical illumination characteristics of a photodiode and explain the operation of the device.	7
8.	a)	Sketch the construction of a silicon controlled rectifier. Also, sketch the two-transistor equivalent circuit and show how it is derived from SCR construction. Label all terminals and explain how the device operates.	7
	b)	Explain with the help of a block diagram, the trigger operation of a CRO.	7
	c)	i) Draw the general structure of a semiconductor IR Emitter Diode and explain the same.	
		ii) Sketch typical radiant-flux-DC forward current characteristics for an IR	